

PCN Number:	20181116001.1		PCN Date:	Nov 19 2018																			
Title:	Qualification of additional Fab site (RFAB) and Assembly/Test site (AP1) options for the TLV6002 device family																						
Customer Contact:	PCN Manager		Dept:	Quality Services																			
Proposed 1st Ship Date:	Feb 19 2019		Estimated Sample Availability:	Date provided at sample request.																			
Change Type:																							
☒	Assembly Site	☒	Assembly Process	☒	Assembly Materials																		
☐	Design	☐	Electrical Specification	☐	Mechanical Specification																		
☒	Test Site	☐	Packing/Shipping/Labeling	☐	Test Process																		
☐	Wafer Bump Site	☐	Wafer Bump Material	☐	Wafer Bump Process																		
☒	Wafer Fab Site	☒	Wafer Fab Materials	☐	Wafer Fab Process																		
	☐	Part number change																					
PCN Details																							
Description of Change:																							
Texas Instruments is pleased to announce the qualification of additional Fab site (RFAB) and Assembly/Test site (AP1) options for the TLV6002 device family.																							
<table border="1" style="margin: auto;"> <tr> <th colspan="6">Additional Fab Site</th> </tr> <tr> <th>Fab Site</th> <th>Process</th> <th>Wafer Diameter</th> <th>Fab Site</th> <th>Process</th> <th>Wafer Diameter</th> </tr> <tr> <td>DP1DM5</td> <td>HPA07</td> <td>200 mm</td> <td>RFAB</td> <td>LBC9</td> <td>300 mm</td> </tr> </table>						Additional Fab Site						Fab Site	Process	Wafer Diameter	Fab Site	Process	Wafer Diameter	DP1DM5	HPA07	200 mm	RFAB	LBC9	300 mm
Additional Fab Site																							
Fab Site	Process	Wafer Diameter	Fab Site	Process	Wafer Diameter																		
DP1DM5	HPA07	200 mm	RFAB	LBC9	300 mm																		
Assembly construction differences are as follows (TLV6002IDR only):																							
		Current	Additional																				
Mount Compound		4147858	SID#101375281																				
Mold Compound		4211880	SID#101380756																				
Bond wire composition/diameter		Au/0.96 mils	Au/0.96 mils or Cu/1.0 mils																				
Lead Frame Finish		NiPdAu	Matte Sn																				
Test coverage, insertions, conditions will remain consistent with current testing and verified with test MQ.																							
Upon expiration of this PCN, TI will combine lead free solutions in a single standard part number , for example; TLV6002IDR – can ship with both Matte Sn and NiPdAu.																							
Reason for Change:																							
Continuity of Supply																							
Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):																							
None																							
Anticipated impact on Material Declaration																							
☐	No Impact to the Material Declaration	☒	Material Declarations or Product Content reports are driven from production data and will be available following the production release. Upon production release the revised reports can be obtained from the TI ECO website .																				

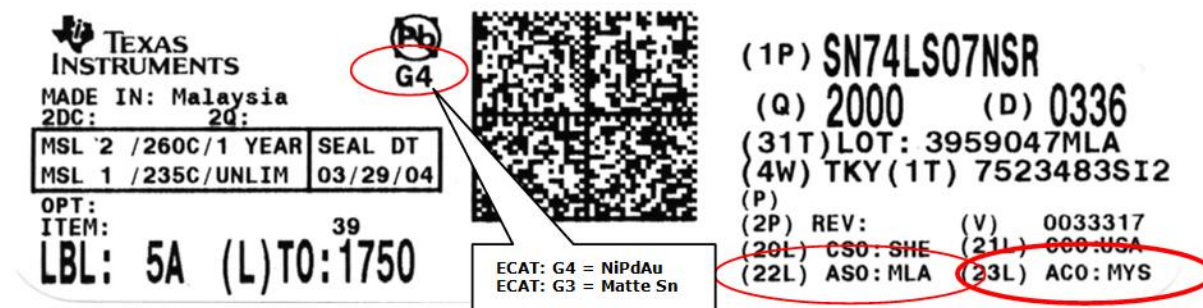
Changes to product identification resulting from this PCN:**Fab Site Information:**

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DP1DM5	DM5	USA	Dallas
RFAB	RFB	USA	Richardson

Assembly Site Information:

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (21L)	Assembly City
TI Mexico	MEX	MEX	Aguascalientes
Amkor Phi	AKR	PHL	Cupang, Muntinlupa City

Sample product shipping label (not actual product label)

**Product Affected:****Group 1 Device list (Additional RFAB Fab site qualification only):**

TLV6002IDGKR	TLV6002IDGKT
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Group 2 Device list (Additional RFAB Fab and Assembly AP1 site Qualification):

TLV6002IDR



Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	Test Name / Condition	Duration	Qual Device: TLV6002IDGKR	QBS Product Reference: TLV6002IDR	QBS Process Reference: TLV9062ID	QBS Package Reference: TLV9062IDGK
ED	Electrical Characterization	Per Datasheet Parameters	Pass	Pass	Pass	Pass
ELFR	Early Life Failure Rate, 125C	48 Hours	-	-	3/2399/0	-
HAST	Biased HAST, 130C/85%RH	96 Hours	-	1/77/0	3/231/0	3/231/0
HBM	ESD - HBM	2000 V	-	1/3/0	3/9/0	-
CDM	ESD - CDM	1000 V	1/3/0	1/3/0	3/9/0	-
HTOL	Life Test, 150C	300 Hours	-	1/77/0	3/231/0	-
HTSL	High Temp Storage Bake 170C	420 Hours	-	1/77/0	3/231/0	3/230/0
LU	Latch-up	(per JESD78)	-	1/6/0	3/18/0	-
SD	Solderability	Pb Free	-	-	3/66/0	3/66/0
TC	Temperature Cycle, -65/150C	500 Cycles	1/77/0	1/76/0	3/231/0	3/231/0
UHAST	Unbiased HAST, 130C/85%RH	96 Hours	-	1/77/0	3/231/0	3/231/0

- QBS: Qual By Similarity
- Qual Device TLV6002IDGKR is qualified at LEVEL2-260C
- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com